

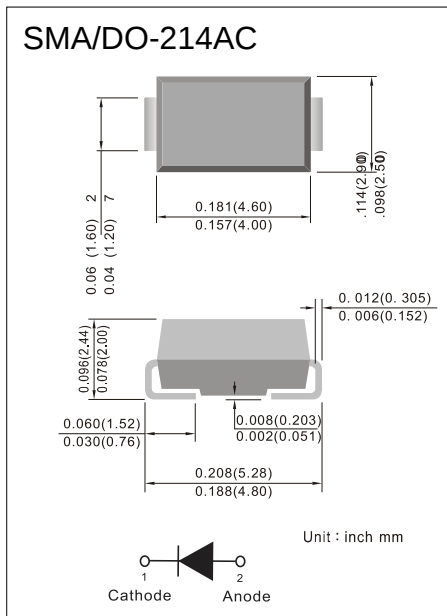
Surface Mount Schottky Barrier Diode

Features

- Low profile package
- Ideal for automated placement
- Guardring for overvoltage protection
- Low power losses, high efficiency
- High forward surge capability
- AEC-Q101 qualified
- Compliant with RoHS standards, halogen-free

Mechanical Data

- **Package:** SMA/DO-214AC
- **Terminal:** Tin plated leads, solderable per
- **Polarity:** Cathode line denotes the cathode end



Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Unit	SS								
			22AQ	23AQ	24AQ	25AQ	26AQ	28AQ	210AQ	215AQ	220AQ
Repetitive Peak Reverse Voltage	V _{RRM}	V	20	30	40	50	60	80	100	150	200
Average Rectified Output Current @60Hz Half-sine wave, Resistance load, TL (FIG.1)	I _O	A	2.0								
Surge(Non-repetitive)Forward Current @60Hz Half-sine wave, 1 cycle, Ta=25°C	I _{FSM}	A	50								
Junction Temperature	T _j	°C	-55 ~+150					-55 ~+175			
Storage Temperature	T _{stg}	°C	-55 ~+150								

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Unit	Test Conditions	SS									
				22AQ	23AQ	24AQ	25AQ	26AQ	28AQ	210AQ	215AQ	220AQ	
Maximum instantaneous forward voltage drop per diode	V _F	V	I _{FM} =2.0A	0.55			0.70		0.85		0.95		
Maximum DC reverse current at rated DC blocking voltage per diode@ V _{RM} =V _{RRM}	I _{RRM}	mA	Ta=25°C	0.50					0.10				
			Ta=100°C	10					5				



Thermal Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Unit	SS								
			22AQ	23AQ	24AQ	25AQ	26AQ	28AQ	210AQ	215AQ	220AQ
Thermal Resistance	$R_{\theta\text{JA}}^{(1)}$	$^{\circ}\text{C/W}$	75								
	$R_{\theta\text{JL}}^{(1)}$		17								

Note

(1) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas

Characteristics (Typical)

